

Abstract

The invention relates to nano-wires which consist of or
comprise semiconductor materials and are used for
5 applications in photovoltaics and electronics and to a
method for the production thereof. The nano-wires are
characterized in that they are obtained by a novel
method using novel precursors. The precursors represent
compounds, or mixtures of compounds, each having at
10 least one direct Si-Si and/or Ge-Si and/or Ge-Ge bond,
the substituents of which consist of halogen and/or
hydrogen, and in the composition of which the atomic
ratio of substituent:metalloid atoms is at least 1:1.



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